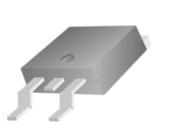
Analog Power AM30N10-50D

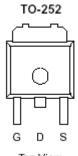
## N-Channel 100-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

| PRODUCT SUMMARY     |                        |            |  |
|---------------------|------------------------|------------|--|
| V <sub>DS</sub> (V) | $r_{DS(on)} m(\Omega)$ | $I_{D}(A)$ |  |
| 100                 | $50 @ V_{GS} = 10V$    | 26         |  |
| 100                 | $59 @ V_{GS} = 4.5V$   | 24         |  |

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology





| -   |     |      |
|-----|-----|------|
| Lor | ١V  | LCOU |
| 100 | , v | 164  |
|     |     |      |

| ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED) |                      |                                   |            |       |  |
|--|----------------------|-----------------------------------|------------|-------|--|
| Parameter  |                      | Symbol                            | Limit      | Units |  |
| Drain-Source Voltage   |                      | $V_{DS}$                          | 100        | V     |  |
| Gate-Source Voltage  |                      | $V_{GS}$                          | ±20        | V     |  |
| Continuous Drain Current <sup>a</sup>                                    | T <sub>C</sub> =25°C | $I_{\mathrm{D}}$                  | 20         |       |  |
| Pulsed Drain Current <sup>b</sup>  |                      |                                   | 36         | A     |  |
| Continuous Source Current (Diode Conduction) <sup>a</sup>                |                      | $I_S$                             | 30         | Α     |  |
| Power Dissipation <sup>a</sup>   | Tc=25°C              | $P_{\mathrm{D}}$                  | 50         | W     |  |
| Operating Junction and Storage Temperature Range                         |                      | T <sub>J</sub> , T <sub>stg</sub> | -55 to 175 | °C    |  |

| THERMAL RESISTANCE RATINGS               |                |         |       |  |
|--|----------------|---------|-------|--|
| Parameter                                | Symbol         | Maximum | Units |  |
| Maximum Junction-to-Ambient <sup>a</sup> | $R_{	heta JA}$ | 50      | °C/W  |  |
| Maximum Junction-to-Case                 | $R_{	heta JC}$ | 3.0     | °C/W  |  |

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## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Analog Power AM30N10-50D

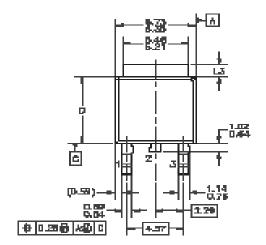
| SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED) |  |  |        |     |      |      |  |
|---|--|--|--------|-----|------|------|--|
| Parameter   | Symbol                                       | Test Conditions  | Limits |     |      | Unit |  |
| 1 ai aine te i  | Symbol                                       | Test Conditions  | Min    | Тур | Max  | Unit |  |
| Static  |  |  |        |     |      |      |  |
| Gate-Threshold Voltage  | $V_{GS(th)}$                                 | $V_{DS} = V_{GS}, I_D = 250 \mathrm{uA}$   | 1.0    |     |      | V    |  |
| Gate-Body Leakage   | I <sub>GSS</sub>                             | $V_{DS} = 0 \text{ V}, V_{GS} = 20 \text{ V}$  |        |     | ±100 | nA   |  |
| Zero Gate Voltage Drain Current                               | $I_{DSS}$                                    | $V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$  |        |     | 1    | uA   |  |
| Zero Gate Voltage Diam Current                                | IDSS   | $V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$              |        |     | 25   |      |  |
| On-State Drain Current <sup>A</sup>                           | $I_{D(on)}$                                  | $V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$  | 34     |     |      | A    |  |
| A   | <b>**</b> ********************************** | $V_{GS} = 10 \text{ V}, I_D = 9.2 \text{ A}$   |        |     | 50   | mΩ   |  |
| Drain-Source On-Resistance <sup>A</sup>                       | fDS(on)                                      | $V_{GS} = 4.5 \text{ V}, I_D = 6.1 \text{ A}$  |        |     | 59   |      |  |
| Forward Tranconductance <sup>A</sup>                          | $g_{\mathrm{fs}}$                            | $V_{DS} = 40 \text{ V}, I_D = 5.5 \text{ A}$   |        | 4.4 |      | S    |  |
| Diode Forward Voltage   | $V_{\mathrm{SD}}$                            | $I_S = 9 A, V_{GS} = 0 V$  |        | 1.1 |      | V    |  |
| Dynamic <sup>b</sup>  |  |  |        |     |      |      |  |
| Total Gate Charge   | Qg   | $V_{DS} = 25 \text{ V}, V_{GS} = 10 \text{ V},$  |        | 25  |      |      |  |
| Gate-Source Charge  | $Q_{gs}$                                     | VDS = 25  V,  VGS = 10  V, $ID = 9  A$   |        | 5   |      | nC   |  |
| Gate-Drain Charge   | $Q_{gd}$                                     |  |        | 19  |      |      |  |
| Turn-On Delay Time  | t <sub>d(on)</sub>                           |  |        | 9   |      |      |  |
| Rise Time   | $t_{\rm r}$                                  | $V_{DD} = 100 \text{ V}, R_L = 25 \Omega, I_D = 9 \text{ A},$ $V_{GEN} = 10 \text{ V}$ |        | 15  |      | nS   |  |
| Turn-Off Delay Time   | t <sub>d(off)</sub>                          |  |        | 45  |      |      |  |
| Fall-Time   | tf   |  |        | 39  |      |      |  |

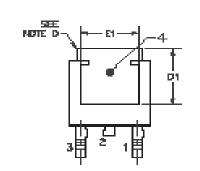
## Notes

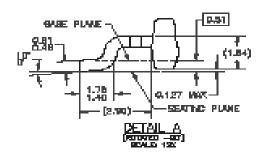
- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

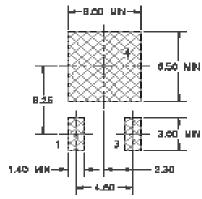
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## Package Information

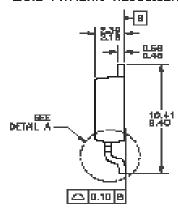








LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

- ALL DIPERSONS ARE IN INCLINETERS.
  THIS PRODUCE CONFORMS TO JEDEC, TO-262,
  188UE C, VARIATION AS IN 68, DATED NOW 1989.
  DIMENSIONING AND TOLERANGING PER
- MANE THANH-1884.
  HEAT SINK TOP EDGE COULD BE IN CHANFERED
  CORRESS OR EDGE PROTRUSION.
  DIMENSIONS 13,0,61401 TABLE:

|      | OPTION JA | OFFICE AD |
|------|-----------|-----------|
|      | 0.0 -1.27 | 1.62-7.09 |
|      |           | 8.44-8.40 |
|      | 4.42      | 3.81 MM   |
| BI I |           | 4 400 100 |